

LN6263

Silicon Schottky Barrier Diodes
for general purpose applications

Special Features:
Low Forward Voltage
Subnanosecond Switching
Glass Hermetic Package

Description

The LN6263 is a metal on silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications.

Glass case JEDEC DO-35 package

Package Specifications

Lead Material	Iron Core, Copper Clad, Tin Plated
Axial Lead Stress	10lbs. max.
Package Inductance	1.8nH typ.
Package Capacitance	0.25 pF typ.

Absolute Maximum Ratings

	Symbol	Value	Unit
Peak Inverse Voltage	PIV	60	V
Power Dissipation (Infinite Heatsink)	P _{tot}	400	mW
Max. Single Cycle Surge 10us Squarewave	I _{FSM}	2	A
Operating and Storage Temperature	T _j , T _s	200	C

Characteristics at T_j = 25 C

	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at I _r = 10 uA	V(BR)R	60	-	-	V
Leakage Current at V _r = 50V	I _r	-	-	200	nA
Forward Voltage Drop at I _f = 1mA	V _f	-	-	0.41	V
at I _f = 15mA	V _f	-	-	1	V
Junction Capacitance at V _r = 0, f = 1 MHz	C _t	-	-	2.2	pF
Reverse Recovery Time at I _f = I _r = 5mA, recover to 0.1 I _r	t _{rr}	-	-	1	ns